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APPLICATION NO.	PPLICATION NO. FILING DATE		FIRST NAMED INVENTOR	ATTORNEY DOCKET NO.	CONFIRMATION NO.
09/732,468		12/07/2000	Christopher Mark Bowles	TI-24521	3187
23494	7590	07/23/2002			
		ENTS INCORPOR	EXAMINER		
P O BOX 65 DALLAS, T	•		PEREZ RAMOS, VANESSA		
				ART UNIT	PAPER NUMBER
				1765	_
				DATE MAILED: 07/23/2002	1

Please find below and/or attached an Office communication concerning this application or proceeding.

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	Application No.	Applicant(s)	<u>v 11</u>			
	09/732,468	BOWLES ET AL.				
Office Action Summary	Examiner	Art Unit				
	Vanessa Perez-Ramos	1765				
The MAILING DATE of this communication ap			ress			
Period for Reply  A SHORTENED STATUTORY PERIOD FOR REPL THE MAILING DATE OF THIS COMMUNICATION.  - Extensions of time may be available under the provisions of 37 CFR 1.  after SIX (6) MONTHS from the mailing date of this communication.  - If the period for reply specified above is less than thirty (30) days, a rep  - If NO period for reply is specified above, the maximum statutory period  - Failure to reply within the set or extended period for reply will, by statute  - Any reply received by the Office later than three months after the mailin earned patent term adjustment. See 37 CFR 1.704(b).  Status	136(a). In no event, however, may a reply b ly within the statutory minimum of thirty (30) will apply and will expire SIX (6) MONTHS t e, cause the application to become ABANDO	e timely filed  days will be considered timely. rom the mailing date of this com  DNED (35 U.S.C. § 133).	munication.			
1) Responsive to communication(s) filed on 28	March 2002 .					
<u></u>	his action is non-final.					
3) Since this application is in condition for allow		, prosecution as to the	merits is			
closed in accordance with the practice under Disposition of Claims						
4) Claim(s) 1-21 is/are pending in the application	n.					
4a) Of the above claim(s) is/are withdra	wn from consideration.					
5) Claim(s) is/are allowed.						
6)⊠ Claim(s) <u>1-21</u> is/are rejected.						
7) Claim(s) is/are objected to.						
8) Claim(s) are subject to restriction and/o	or election requirement.					
9) The specification is objected to by the Examine	er.					
10) ☐ The drawing(s) filed on is/are: a) ☐ acce	pted or b) objected to by the E	xaminer.				
Applicant may not request that any objection to the	ne drawing(s) be held in abeyance.	See 37 CFR 1.85(a).				
11) The proposed drawing correction filed on	_ is: a)□ approved b)□ disap	proved by the Examiner				
If approved, corrected drawings are required in re						
12) The oath or declaration is objected to by the Ex	kaminer.					
Priority under 35 U.S.C. §§ 119 and 120						
13) Acknowledgment is made of a claim for foreig	n priority under 35 U.S.C. § 11	9(a)-(d) or (f).				
a) ☐ All b) ☐ Some * c) ☐ None of:						
1. Certified copies of the priority documen	ts have been received.					
2. Certified copies of the priority documen	ts have been received in Applic	cation No				
3. Copies of the certified copies of the prication from the International But See the attached detailed Office action for a list	ureau (PCT Rule 17.2(a)).		tage			
14) Acknowledgment is made of a claim for domest	ic priority under 35 U.S.C. § 11	9(e) (to a provisional a	pplication).			
a) ☐ The translation of the foreign language provisional application has been received.  15)☐ Acknowledgment is made of a claim for domestic priority under 35 U.S.C. §§ 120 and/or 121.						
Attachment(s)						
1) Notice of References Cited (PTO-892) 2) Notice of Draftsperson's Patent Drawing Review (PTO-948) 3) Information Disclosure Statement(s) (PTO-1449) Paper No(s)	5) 🔲 Notice of Inform	nary (PTO-413) Paper No(s) nal Patent Application (PTO-				
U.S. Patent and Trademark Office PTO-326 (Rev. 04-01)  Office A	ction Summary	Part of F	Paper No. 7			

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#### DETAILED ACTION

#### Claim Rejections - 35 USC § 102

1. The following is a quotation of the appropriate paragraphs of 35 U.S.C. 102 that form the basis for the rejections under this section made in this Office action:

A person shall be entitled to a patent unless -

(e) the invention was described in a patent granted on an application for patent by another filed in the United States before the invention thereof by the applicant for patent, or on an international application by another who has fulfilled the requirements of paragraphs (1), (2), and (4) of section 371(c) of this title before the invention thereof by the applicant for patent.

The changes made to 35 U.S.C. 102(e) by the American Inventors Protection Act of 1999 (AIPA) do not apply to the examination of this application as the application being examined was not (1) filed on or after November 29, 2000, or (2) voluntarily published under 35 U.S.C. 122(b). Therefore, this application is examined under 35 U.S.C. 102(e) prior to the amendment by the AIPA (pre-AIPA 35 U.S.C. 102(e)).

2. Claims 1-2, 6-9, 13 and 17-18 are rejected under 35 U.S.C. 102(e) as being anticipated by Lin et al. (U.S. 6,057,207).

Lin discloses a method for forming a shallow trench isolation (col. 2, line 25) comprising: forming a plurality of isolation trenches in substrate, the trenches separating active areas (col. 2, lines 44-51); forming an insulating layer over the substrate, the insulating layer being silicon oxide (col. 2, line 53); filling the trenches and covering the active areas (col. 2, lines 52-55); forming a conformal barrier layer, which reads on Applicant's "planarization layer" on the insulating layer (col. 2, lines 57-61); removing the planarization layer and insulating layer (col. 2, lines 62-67 and col. 3, lines 1-8) down to a stop layer for the active areas (col. 7, lines 44-45). Furthermore, Lin discloses that the step of removing the planarization and insulation layers further comprise etching at a certain rate through the planarization layer and the insulation layer

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down to a certain depth, which reads on Applicant's "down to a CMP depth outward from the active areas" (col. 2, lines 62-67, col. 3, lines 1-2 and col. 6, lines 52-54) and then chemical mechanical polishing from there to the stop layer (col. 3, lines 3-8), said etch stop layer comprising silicon nitride (col. 7, lines 47-48) and being later removed (col. 7, lines 46-47).

### Claim Rejections - 35 USC § 103

- 3. The following is a quotation of 35 U.S.C. 103(a) which forms the basis for all obviousness rejections set forth in this Office action:
  - (a) A patent may not be obtained though the invention is not identically disclosed or described as set forth in section 102 of this title, if the differences between the subject matter sought to be patented and the prior art are such that the subject matter as a whole would have been obvious at the time the invention was made to a person having ordinary skill in the art to which said subject matter pertains. Patentability shall not be negatived by the manner in which the invention was made.
- 4. Claims 3-5, 10-12, 14-16 and 19-21 are rejected under 35 U.S.C. 103(a) as being unpatentable over Lin et al. (U.S. 6,057,207), as applied to claims 1-2, 6-9, 13 and 17-18 above.

In regard to claims 3-5, 14-16 and 21, Lin does not disclose that etching through the insulating and planarizing layers is done by an etch process that etches both layers at differing rates.

However, it is the Examiner's position that, since etching rate is a result-effective variable, its variation would have been obvious to one of ordinary skill in the art at the time of the invention, with the purpose of establishing the optimum process conditions.

In regard to claims 10 and 19, it is the Examiner's position that the use of a resist material would have been obvious to one of ordinary skill in the art at the time of the invention, since this is a widely-used material in the art.

In regard to claims 11 and 20, Lin does not disclose a preferred etching depth.

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However, it is the Examiner's position that, since depth is a result-effective variable, its variation would have been obvious to one of ordinary skill in the art at the time of the invention, with the purpose of establishing the optimum process conditions.

In regard to claim 12, the use of conformal layers would have been obvious to one of ordinary skill in the art at the time of the invention, since this is a widely-used material in the art.

## Response to Arguments

5. Applicant's arguments filed 3/28/02 have been fully considered but they are not persuasive.

Applicant argues that Lin teaches away from forming a planarization layer outwardly from the insulation layer. However, the Examiner stands by her earlier position that the barrier layer of Lin reads on what Applicant calls "planarization layer", as both are located in similar positions and perform similar functions.

It is noted that Applicant's arguments with respect to claims 2-21 are based on the same argument discussed above.

6. THIS ACTION IS MADE FINAL. Applicant is reminded of the extension of time policy as set forth in 37 CFR 1.136(a).

A shortened statutory period for reply to this final action is set to expire THREE MONTHS from the mailing date of this action. In the event a first reply is filed within TWO MONTHS of the mailing date of this final action and the advisory action is not mailed until after the end of the THREE-MONTH shortened statutory period, then the shortened statutory period

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will expire on the date the advisory action is mailed, and any extension fee pursuant to 37

CFR 1.136(a) will be calculated from the mailing date of the advisory action. In no event,

however, will the statutory period for reply expire later than SIX MONTHS from the mailing date

of this final action.

7. Any inquiry concerning this communication or earlier communications from the examiner

should be directed to Vanessa Perez-Ramos whose telephone number is 703-306-5510. The

examiner can normally be reached on Mon-Thurs 7:00am-5:30pm.

If attempts to reach the examiner by telephone are unsuccessful, the examiner's

supervisor, Benjamin Utech can be reached on 703-308-3836. The fax phone numbers for the

organization where this application or proceeding is assigned are 703-872-9310 for regular

communications and 703-872-9311 for After Final communications.

Any inquiry of a general nature or relating to the status of this application or proceeding

should be directed to the receptionist whose telephone number is 703-306-5665.

Vanessa Perez-Ramos

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Examiner-

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**VPR** 

July 18, 2002

mon BENJAMIN L. UTECH

SUPERVISORY PATENT EXAMINER

TECHNOLOGY CENTER 1700